PSMN040-100MSE

N-channel 100 V 36.6 mΩ standard level MOSFET in LFPAK33 designed specifically for high power PoE applications

26 March 2013 **Product data sheet**

1. General description

New standards and proprietary approaches are enabling Power-over-Ethernet (PoE) systems capable of delivering up to 90W to each powered device (PD). Such solutions place increased demands on the power sourcing equipment (PSE) in terms of “soft-start”, thermal management and power density requirements.

2. Features and benefits

- Enhanced forward biased safe operating area for superior linear mode operation
- Low Rdson for low conduction losses
- Ultra reliable LFPAK33 package for superior thermal and ruggedness performance
- Very low I_{DSS}

3. Applications

- High power PoE applications (60W and higher)
- IEEE802.3at and proprietary solutions

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	-	100	V
I_D	drain current	$T_j = 25$ °C; $V_{GS} = 10$ V; Fig. 1		-	-	30	A
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; Fig. 2		-	-	91	W
Static characteristics							
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10$ V; $I_D = 10$ A; $T_j = 25$ °C; Fig. 13		-	29.4	36.6	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	$V_{GS} = 10$ V; $I_D = 10$ A; $V_{DS} = 50$ V; $T_j = 25$ °C; Fig. 14; Fig. 15		-	10.7	-	nC
$Q_{G(tot)}$	total gate charge			-	30	-	nC
Avalanche Ruggedness							
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; $I_D = 30$ A; $V_{sup} \leq 100$ V; $R_{GS} = 50$ Ω; unclamped; Fig. 3		-	-	54	mJ

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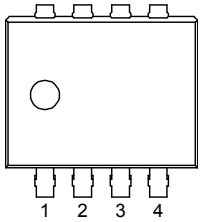
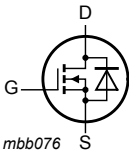
5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 LFPAK33 (SOT1210)	
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN040-100MSE	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 4 leads	SOT1210

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN040-100MSE	M40E10

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	100	V
V_{DGR}	drain-gate voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C; $R_{GS} = 20$ kΩ		-	100	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	$V_{GS} = 10$ V; $T_j = 25$ °C; Fig. 1		-	30	A
		$V_{GS} = 10$ V; $T_{mb} = 100$ °C; Fig. 1		-	21	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10$ µs; $T_{mb} = 25$ °C; Fig. 4		-	121	A
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; Fig. 2		-	91	W
T_{stg}	storage temperature			-55	175	°C

Symbol	Parameter	Conditions		Min	Max	Unit
T_j	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain diode						
I_S	source current	T_{mb} = 25 °C	[1]	-	70	A
I_{SM}	peak source current	pulsed; $t_p \leq 10$ µs; T_{mb} = 25 °C		-	121	A
Avalanche Ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 30 A; $V_{sup} \leq 100$ V; R_{GS} = 50 Ω; unclamped; Fig. 3		-	54	mJ

[1] Continuous current is limited by package.

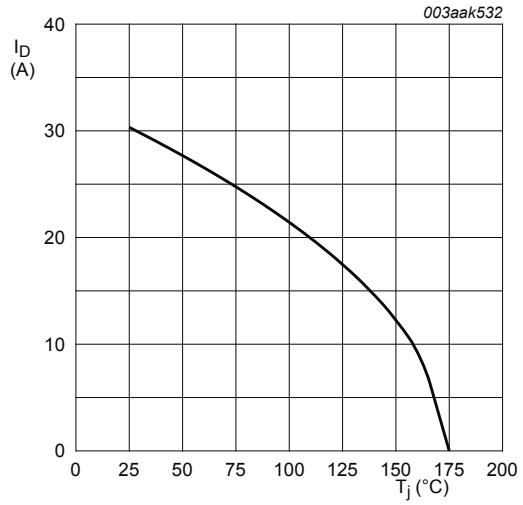


Fig. 1. Continuous drain current as a function of mounting base temperature

$V_{GS} \geq 10V$

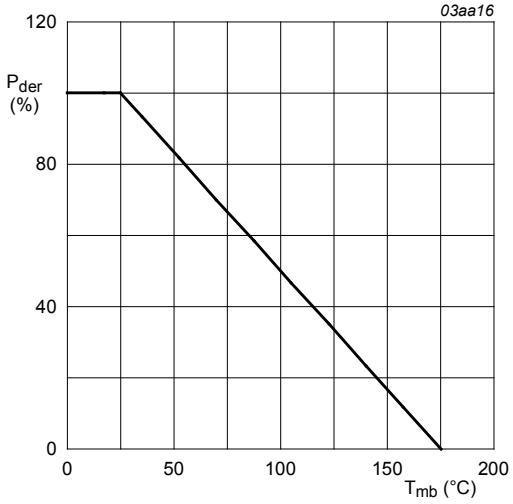


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

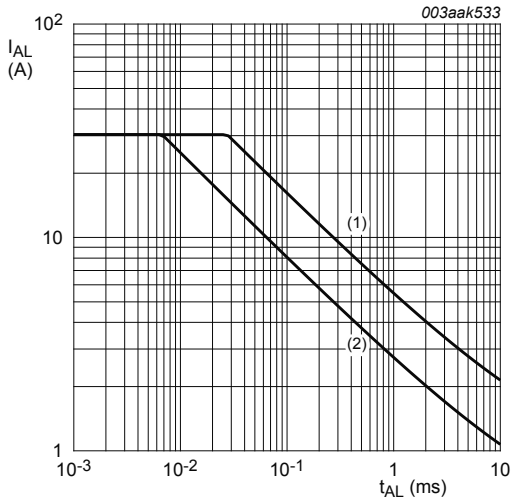


Fig. 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j\ (init)} = 25°C$; (2) $T_{j\ (init)} = 100°C$

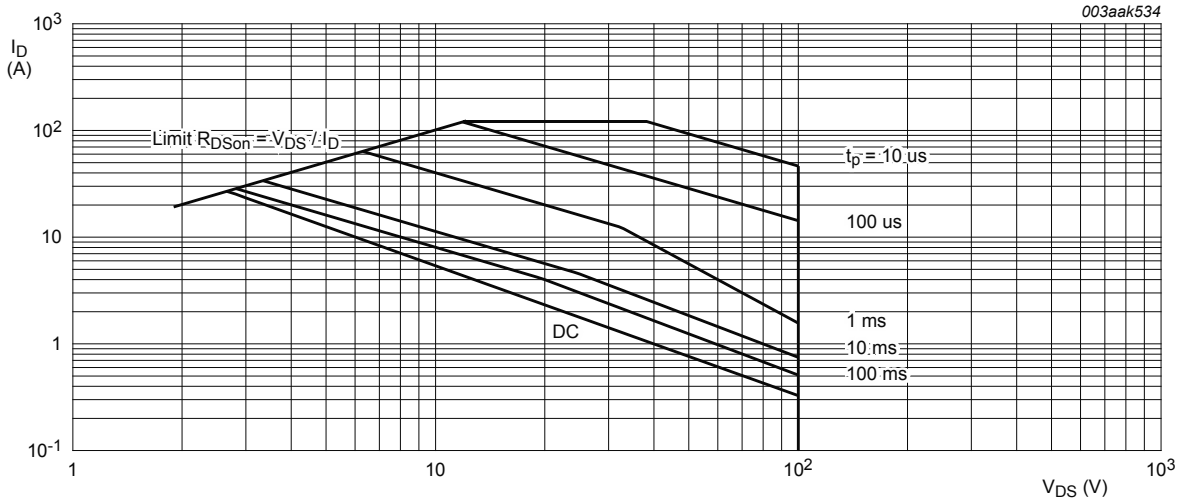


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25°C$; I_{DM} *is a single pulse*

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base	Fig. 5		-	1.44	1.65	K/W

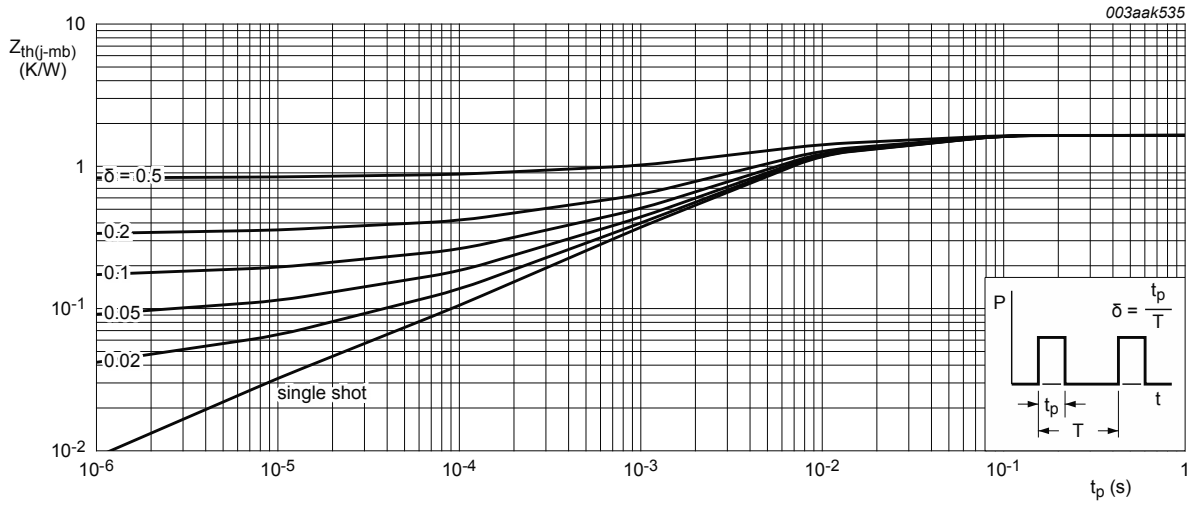


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		100	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; Fig. 10; Fig. 11		2.3	3.3	4	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; Fig. 10		-	-	4.6	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; Fig. 10		1	-	-	V
I_{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C		-	0.05	1	µA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C		-	-	500	µA
I_{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C		-	10	100	nA
		V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C		-	10	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 10 A; T_j = 100 °C; Fig. 12; Fig. 13		-	-	66	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 175 °C; Fig. 12; Fig. 13		-	-	99	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 25 °C; Fig. 13		-	29.4	36.6	mΩ
R_G	gate resistance	f = 10 MHz		-	1.65	-	Ω

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 10 A; V_{DS} = 50 V; V_{GS} = 10 V; T_j = 25 °C; Fig. 14; Fig. 15		-	30	-	nC
		I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V; T_j = 25 °C		-	24	-	nC
Q_{GS}	gate-source charge	I_D = 10 A; V_{DS} = 50 V; V_{GS} = 10 V; T_j = 25 °C; Fig. 14; Fig. 15		-	7.6	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge			-	4.5	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge			-	3.1	-	nC
Q_{GD}	gate-drain charge			-	10.7	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I_D = 10 A; V_{DS} = 50 V; T_j = 25 °C; Fig. 14; Fig. 15		-	5.6	-	V
C_{iss}	input capacitance	V_{DS} = 50 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; Fig. 16		-	1470	-	pF
C_{oss}	output capacitance			-	110	-	pF
C_{rss}	reverse transfer capacitance			-	80	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 50 V; R_L = 5 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 5 Ω; T_j = 25 °C		-	8.3	-	ns
t_r	rise time			-	14.1	-	ns
$t_{d(off)}$	turn-off delay time			-	18.7	-	ns
t_f	fall time			-	13	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	I_S = 20 A; V_{GS} = 0 V; T_j = 25 °C; Fig. 17		-	0.82	1.2	V
t_{rr}	reverse recovery time	I_S = 10 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 50 V; T_j = 25 °C		-	41	-	ns
Q_r	recovered charge			-	75	-	nC

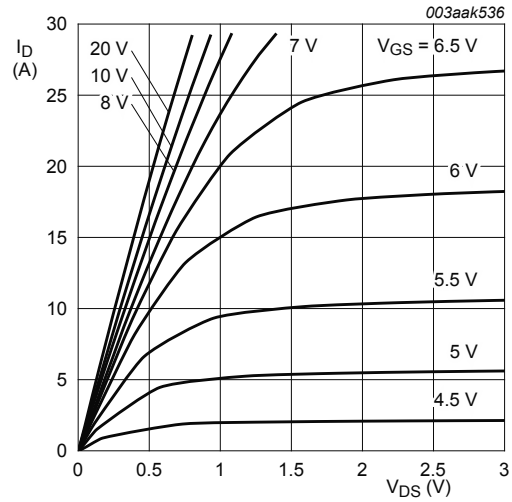


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

$T_j = 25°C$

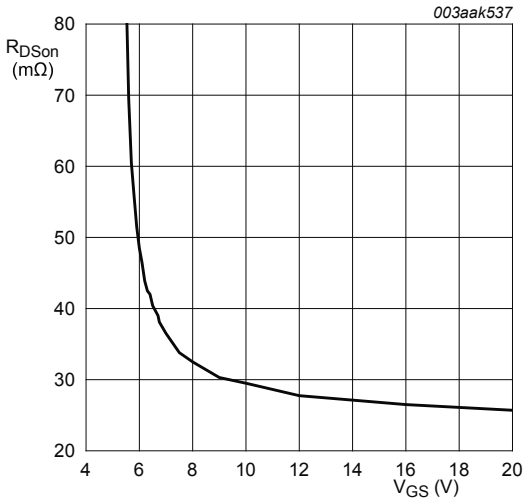


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25°C;\ I_D = 10A$

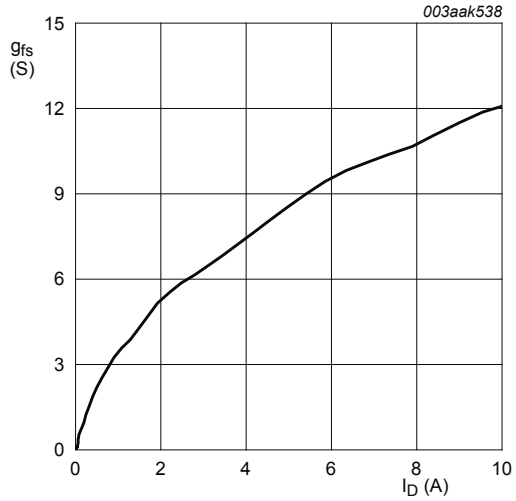


Fig. 8. Forward transconductance as a function of drain current; typical values

$T_j = 25°C;\ V_{DS} = 10V$

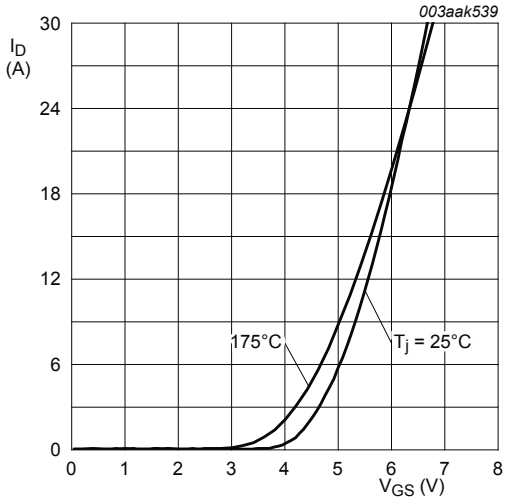


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10V$

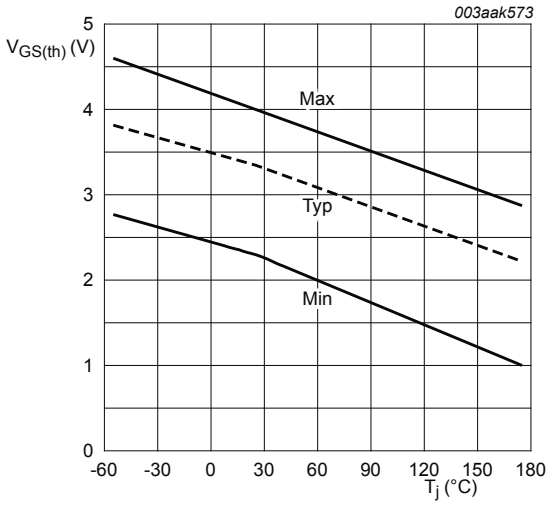


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\ \text{mA};\ V_{DS} = V_{GS}$

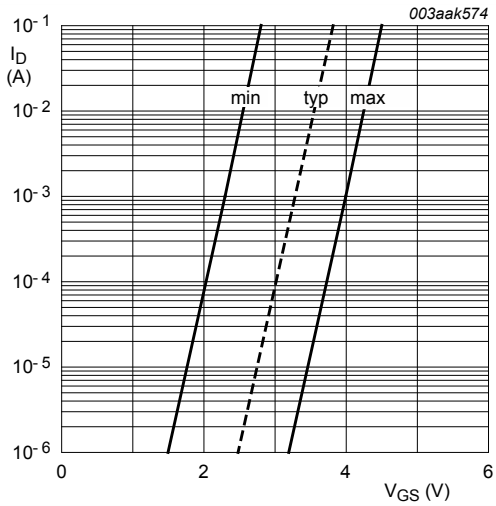


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25\,°C;\ V_{DS} = 5V$

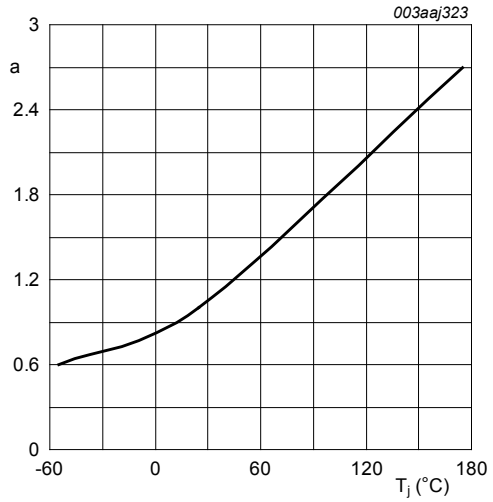


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon\,(25°C)}}$$

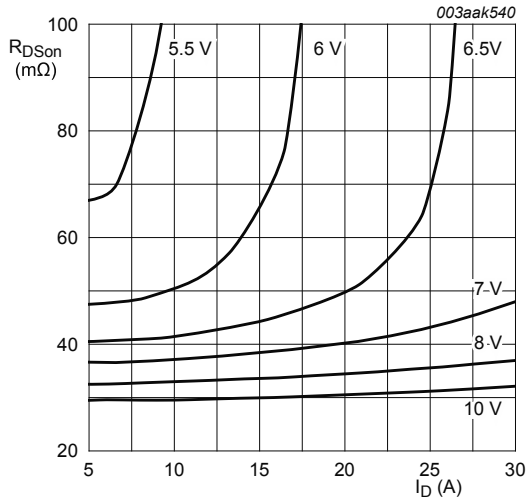


Fig. 13. Drain-source on-state resistance as a function of drain current; typical values

$T_j = 25°C$

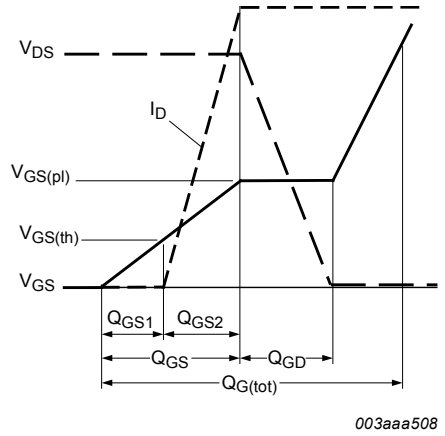


Fig. 14. Gate charge waveform definitions

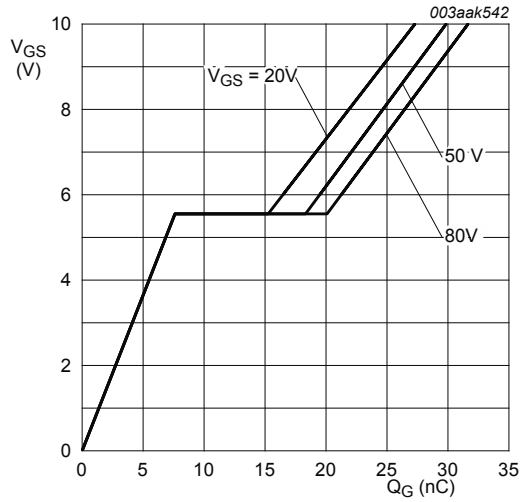


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$T_j = 25°C;\ I_D = 10A$

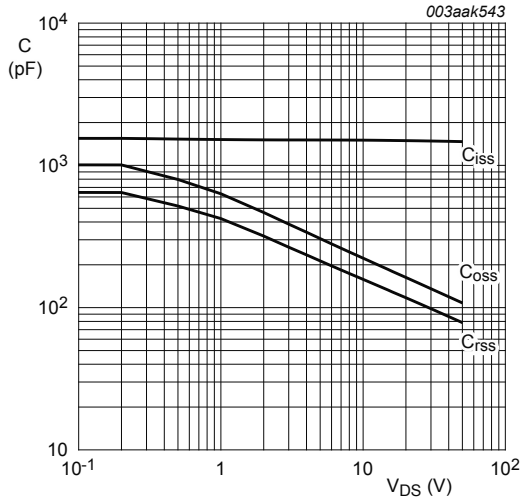


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0V;\ f = 1MHz$

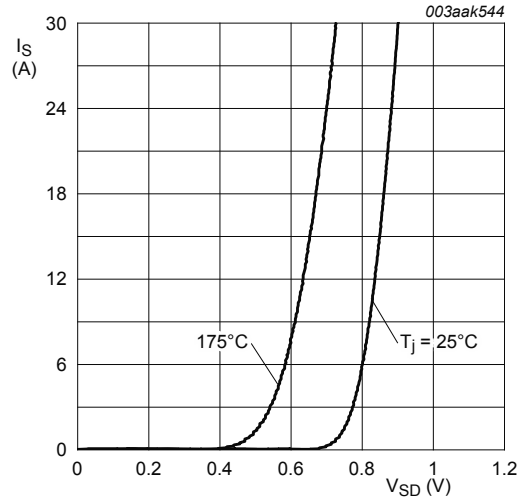
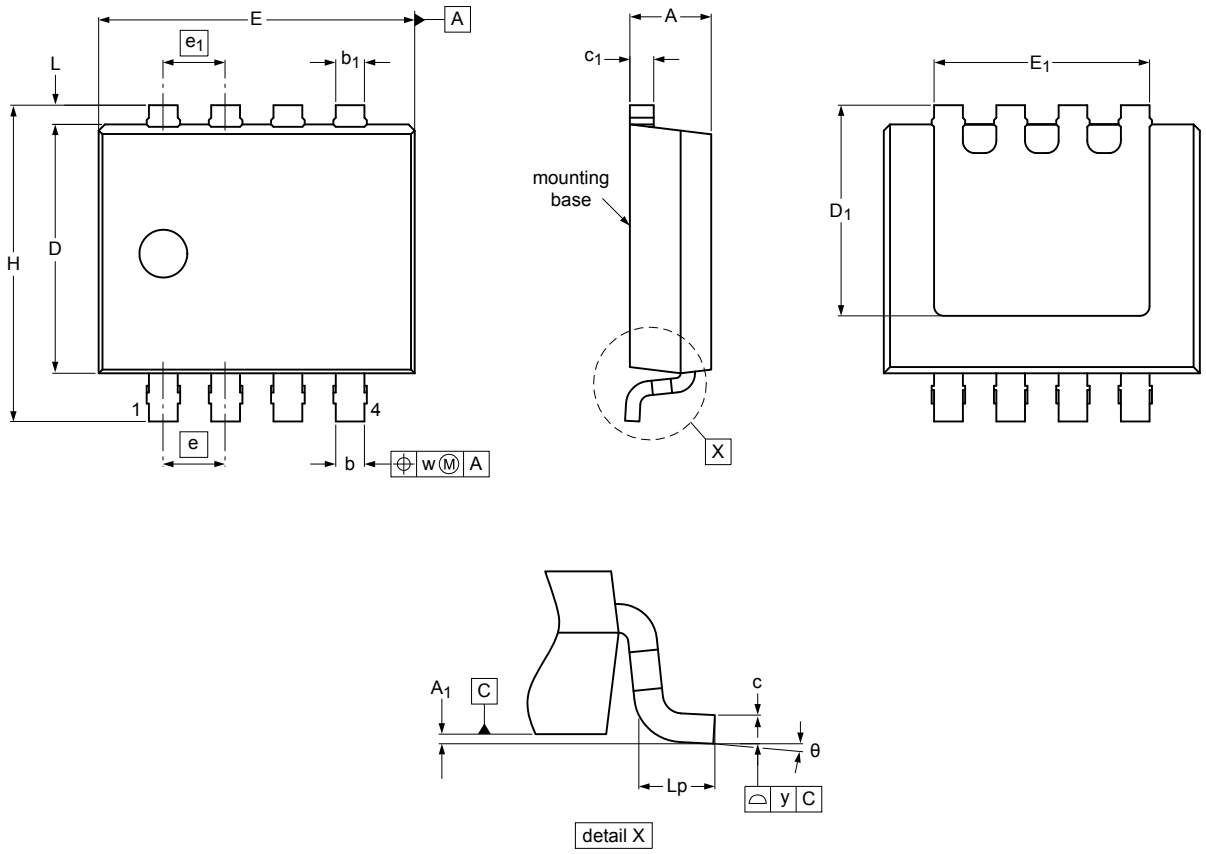


Fig. 17. Source current as a function of source-drain voltage; typical values

$V_{GS} = 0V$

11. Package outline

Plastic single ended surface mounted package (LFPAK33); 8 leads **SOT1210**



Dimensions

Unit(1)		A	A_1	b	b_1	c	c_1	D(1)	D_1	E(1)	E_1	e	e_1	H	L	L_p	w	y	θ
mm	max	0.90	0.10	0.35	0.35	0.20	0.30	2.70	2.35	3.40	2.45			3.40	0.25	0.50			8°
	nom											0.65	0.65				0.20	0.10	
	min	0.80	0.00	0.25	0.25	0.10	0.20	2.50	1.90	3.20	2.00			3.20	0.13	0.30			0°

Note
1. Plastic or metal protrusions of 0.15 mm per side are not included.

sot1210_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1210						~~11-12-19~~ 12-03-12

Fig. 18. Package outline LFPAK33 (SOT1210)

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
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